

STRUCTURE Silicon Monolithic Integrated Circuit

TYPE Reference Voltage Regulator

PRODUCT SERIES **B D 3 5 7 2 F P**

FEATURES 1.Adjustable output voltage/ Low dropout voltage/ Low quiescent current
 2.Built-in Overcurrent protection circuit/ Thermal shutdown circuit

○ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Parameter | Symbol | Limit | Unit |
|------------------------------|--------|----------|------|
| Supply Voltage | Vcc | 50 ※1 | V |
| Power Dissipation | Pd | 1.3 ※2 | W |
| Operating Temperature Range | Topr | -40~+125 | °C |
| Storage Temperature Range | Tstg | -55~+150 | °C |
| Maximum Junction Temperature | Tjmax | 150 | °C |

※1 Not to exceed Pd and ASO.

※2 Reduced by 10.4mW/°C over Ta=25°C , when mount on a glass epoxy board:70mm×70mm×1.6mm.

○OPERATING CONDITIONS

| Parameter | Symbol | Min | Max | Unit |
|----------------|--------|--------|------|------|
| Supply Voltage | Vcc | 4.5 ※3 | 36.0 | V |
| Output Current | Io | — | 500 | mA |
| Output Voltage | Vo | 2.8 | 12 | V |

※3 Please consider that the Output voltage would be dropped (Dropout voltage) according to the Output current.

Status of this document

The Japanese version of this document is the formal specification.

A customer may use this translation version only for a reference to help reading the formal version.

If there are any differences in translation version of this document, formal version takes priority.

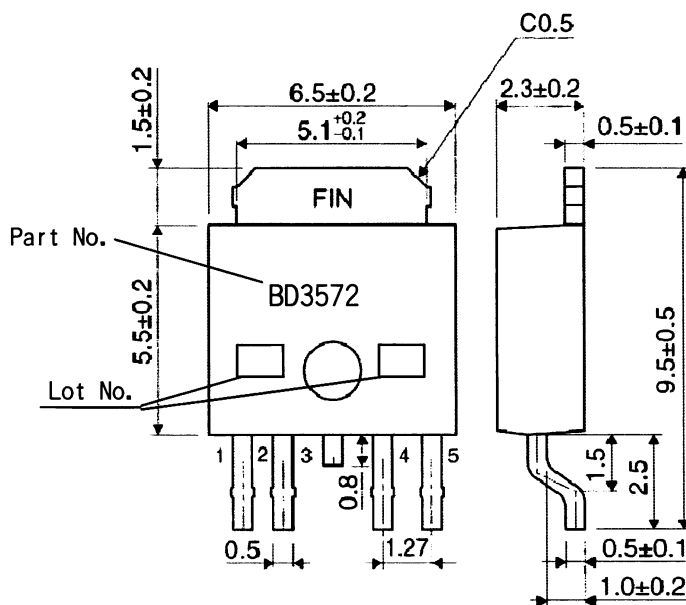
○ELECTRICAL CHARACTERISTICS (Unless otherwise specified, $T_a = -40 \sim 125^\circ\text{C}$, $V_{cc} = 13.2\text{V}$, V_o settings is 5V)

| Parameter | Symbol | Limits | | | Unit | Conditions |
|----------------------|--------------|--------|-------|-------|---------------|--|
| | | MIN | Typ | MAX | | |
| Bias Current | I_b | — | 30 | 50 | μA | $I_o = 0\text{mA}$ |
| ADJ Terminal Voltage | VADJ | 1.235 | 1.260 | 1.285 | V | $I_o = 200\text{mA}$ |
| Output Current | I_o | 0.5 | — | — | A | |
| Dropout Voltage | ΔV_d | — | 0.25 | 0.48 | V | $V_{cc} = 4.75\text{V}$, $I_o = 200\text{mA}$ |
| Ripple Rejection | R. R. | 45 | 55 | — | dB | $f = 120\text{Hz}$, $e_{in} = 1\text{V}_{rms}$, $I_o = 100\text{mA}$ |
| Line Regulation | Reg. I | — | 10 | 30 | mV | $6.5\text{V} \leq V_{cc} \leq 25\text{V}$, $I_o = 0\text{mA}$ |
| Load Regulation | Reg. L | — | 20 | 40 | mV | $0\text{mA} \leq I_o \leq 200\text{mA}$ |

This product is not designed for protection against radio active rays.

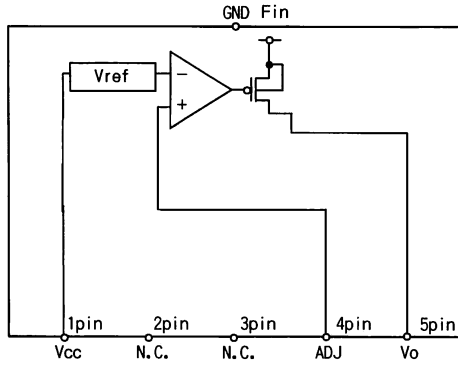
NOTE) All characteristics are measured with $0.33\mu\text{F}$ and $0.1\mu\text{F}$ capacitors connected to input and output pins, respectively. Because measurements (pulse measurements) were taken when $T_a = T_j$, data other than the temperature coefficient of Output voltage does not include fluctuations due to temperature variations.

○PHYSICAL DIMENSIONS • MARKING



T0252-5 (Unit : mm)

○BLOCK DIAGRAM

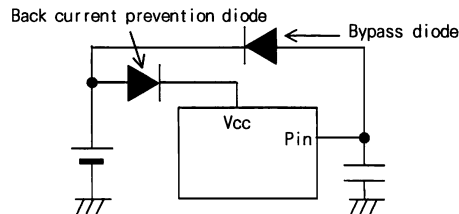


○PIN No. • PIN NAME

| Pin No. | Pin Name |
|---------|----------|
| 1 | Vcc |
| 2 | N.C. |
| 3 | N.C. |
| 4 | ADJ |
| 5 | Vo |
| Fin | GND |

○OPERATING NOTES

- 1) Absolute maximum ratings
Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.
- 2) GND potential
Ensure a minimum GND pin potential in all operating conditions.
- 3) Thermal design
Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.
- 4) Pin short and mistake mounting
Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins and the power supply and GND pins caused by the presence of a foreignobject may result in damage to the IC. Ensure a minimum GND pin potential in all operating conditions.
- 5) Actions in strong magnetic field
Keep in mind that the IC may malfunction in strong magnetic fields.
- 6) Testing on application boards
When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC.
- 7) Ground patterns
When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the application's reference point so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring pattern of any external parts, either.
- 8) Applications or inspection processes where the potentials of the Vcc pin and other pins may be reversed from their normal states may cause damage to the IC's internal circuitry or elements. Use an output pin capacitance of 470 μF or lower in case Vcc is shorted with the GND pin while the external capacitor is charged. It is recommended to insert a diode for preventing back current flow in series with Vcc or bypass diodes between Vcc and each pin.



9) Thermal shutdown circuit (TSD)

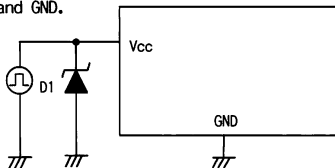
This IC incorporates a built-in TSD circuit for the protection from thermal destruction. The IC should be used within the specified power dissipation range. However, in the event that the IC continues to be operated in excess of its power dissipation limits, the attendant rise in the junction temperature (T_j) will trigger the TSD circuit to turn off all output power elements (175°C:Typ). The circuit automatically resets once the junction temperature (T_j) drops (150°C:Typ). Operation of the TSD circuit presumes that the IC's absolute maximum ratings have been exceeded. Application designs should never make use of the TSD circuit.

10) Overcurrent protection circuit (OCP)

The IC incorporates a built-in overcurrent protection circuit that operates according to the output current capacity. This circuit serves to protect the IC from damage when the load is shorted. The protection circuit is designed to limit current flow by not latching in the event of a large and instantaneous current flow originating from a large capacitor or other component. This protection circuit is effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits. At the time of thermal designing, keep in mind that the current capacity has negative characteristics to temperatures.

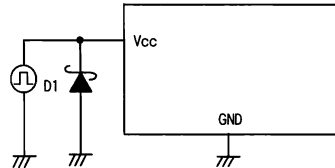
11) About positive surge voltage

To protect against a surge voltage that exceeds 50V between Vcc and GND please insert a power zener diode between Vcc terminal and GND.



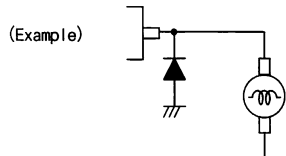
12) About negative surge voltage

To protect against a negative surge voltage, please insert a Schottky diode between the Vcc terminal and GND.



13) We recommend using Diode for protection purpose when the temperature so output voltage is off.

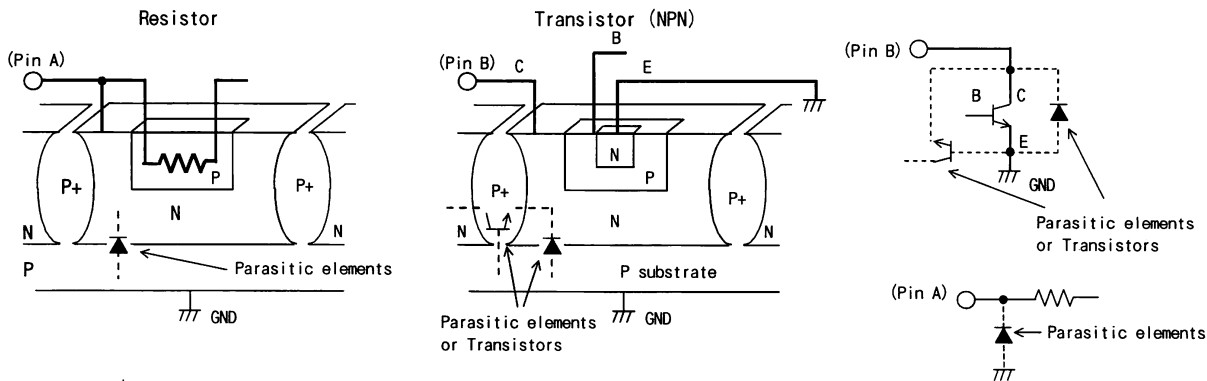
This is to prevent against large loads of impedance or reverse current during initial stages or output off stage.



14) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when the resistors and transistors are connected to the pins as shown in the following figure,

- The P/N junction functions as a parasitic diode when $GND > Pin A$ for the resistor or $GND > Pin B$ for the transistor (NPN).
- Similarly, when $GND > Pin B$ for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the GND (P substrate) voltage to input pins. Keep in mind that the IC may malfunction in strong magnetic fields.



Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

It is our top priority to supply products with the utmost quality and reliability. However, there is always a chance of failure due to unexpected factors. Therefore, please take into account the derating characteristics and allow for sufficient safety features, such as extra margin, anti-flammability, and fail-safe measures when designing in order to prevent possible accidents that may result in bodily harm or fire caused by component failure. ROHM cannot be held responsible for any damages arising from the use of the products under conditions out of the range of the specifications or due to non-compliance with the NOTES specified in this catalog.

Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact your nearest sales office.

ROHM Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

www.rohm.com

Contact us : webmaster@rohm.co.jp